

Fig. 1

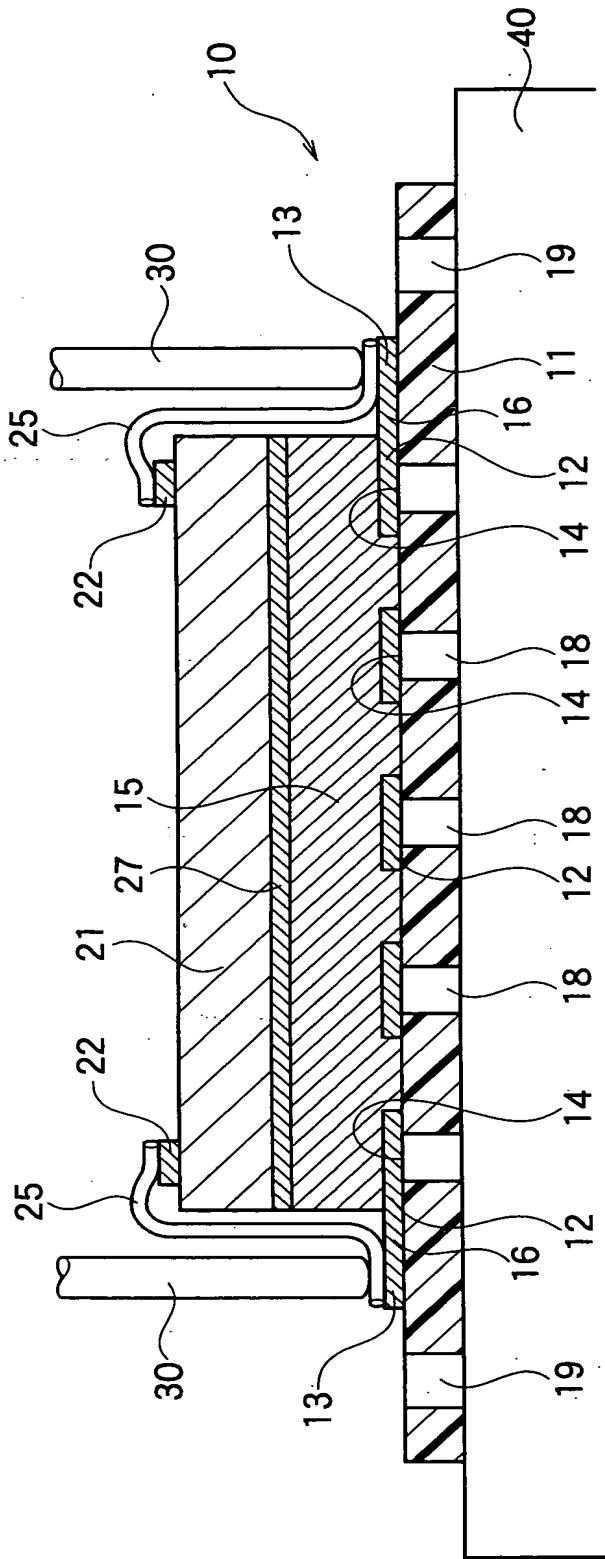
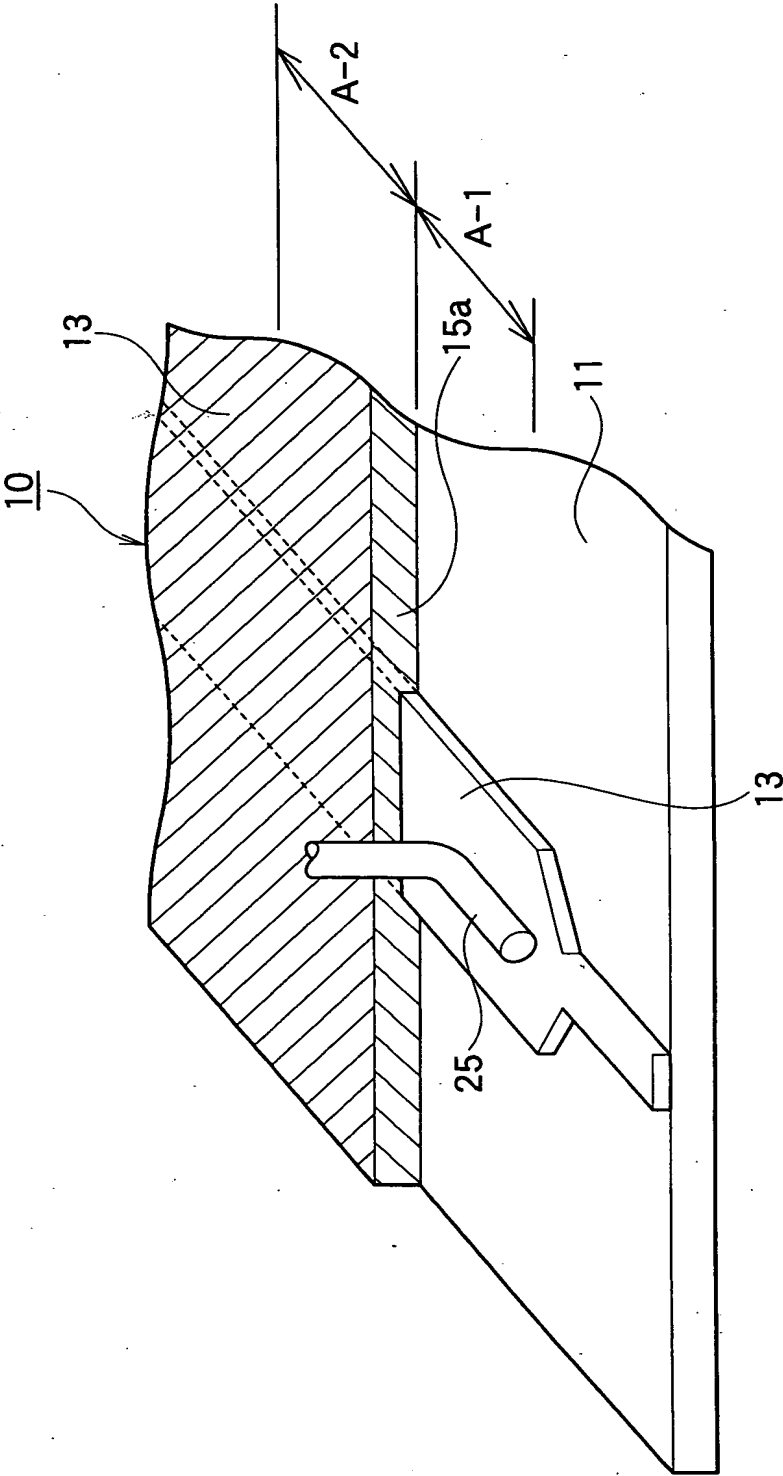


Fig. 2



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Fig. 3

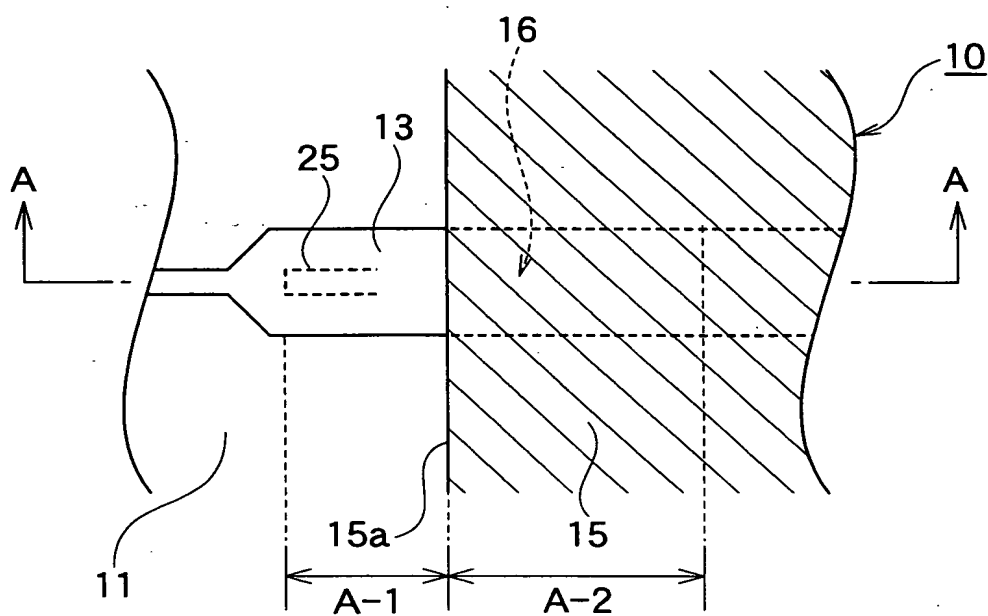
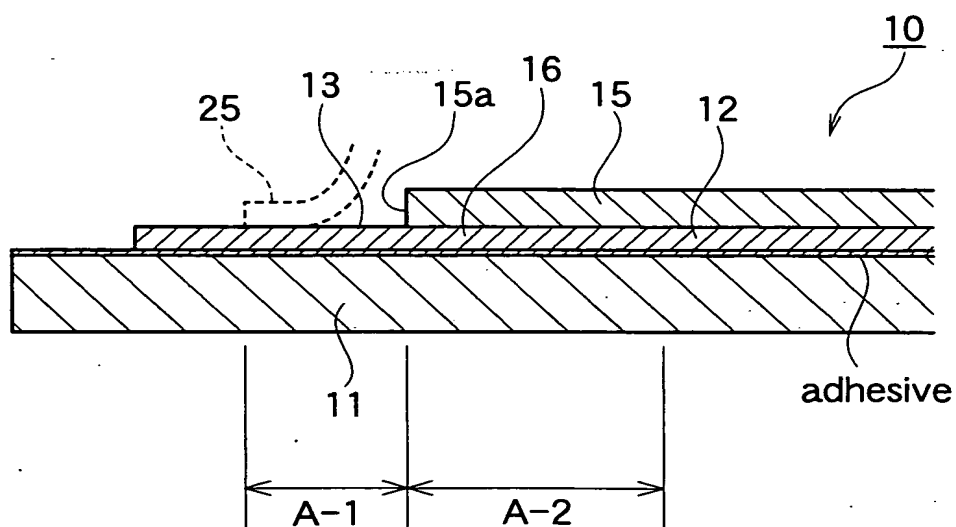
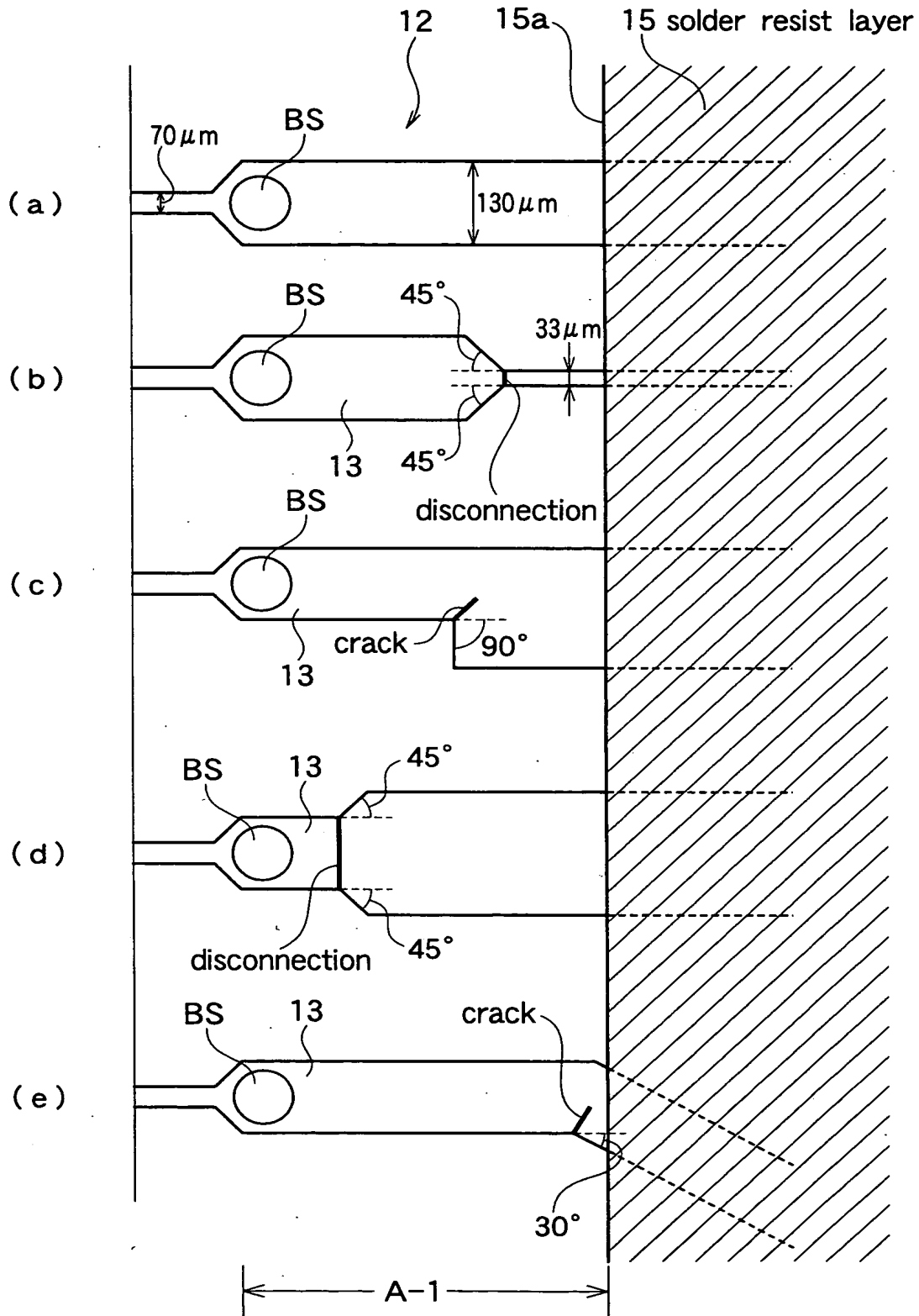


Fig. 4



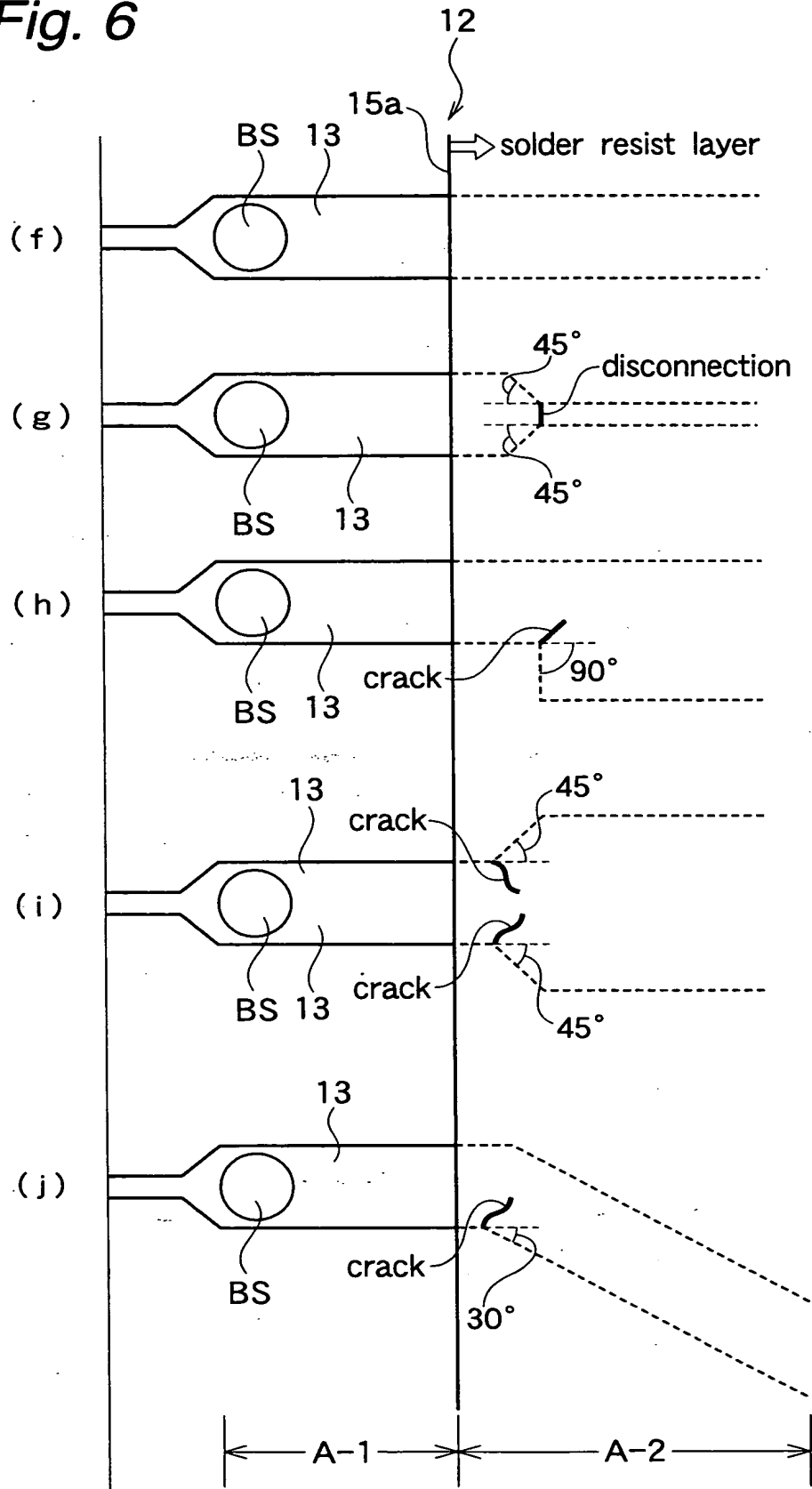
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Fig. 5



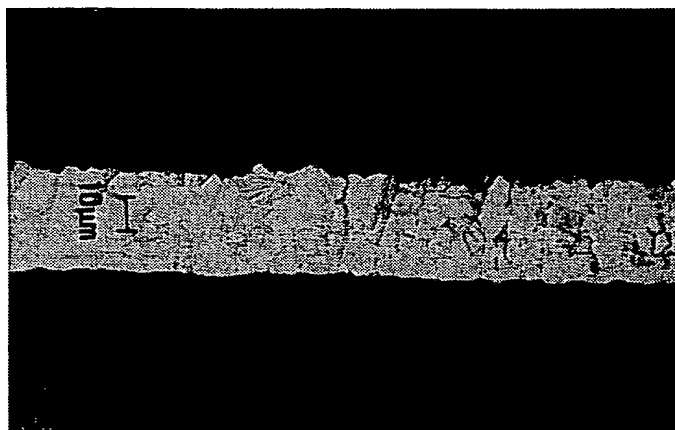
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Fig. 6

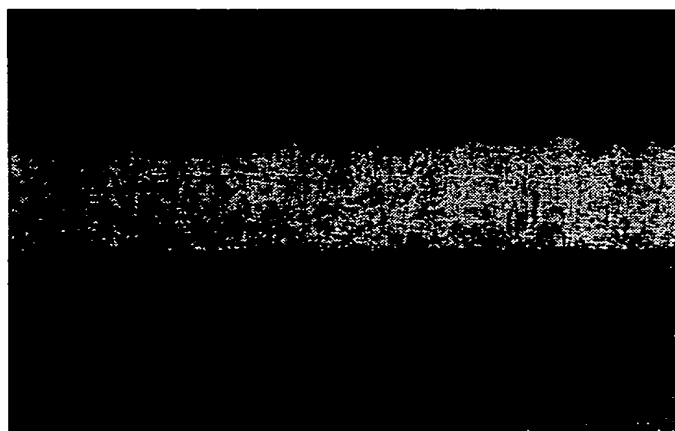


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*Fig. 7*



*Fig. 8*



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A cross-sectional view of a semiconductor device. It features a central trench (25) with a bottom layer (22) and side walls (21). The trench is flanked by two regions (13) containing a layer (15). The entire structure is on a substrate (11) with a top layer (12).

A cross-sectional view of a multi-layered structure. A central block (21) is flanked by two side blocks (11). Each side block (11) has a top layer (12) and a bottom layer (15). A thin layer (13) is positioned between the central block (21) and the side blocks (11). A wavy line (22) is shown on top of the central block (21). A wavy line (25) is shown on top of the side blocks (11).

*Fig. 10*